

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ C$
20V	27m Ω @ $V_{GS} = 4.5V$	5.6
	35m Ω @ $V_{GS} = 2.5V$	4.9

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

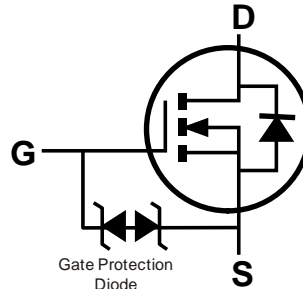
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

Mechanical Data

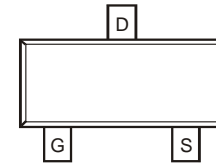
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



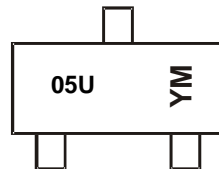
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2025U-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



05U = Product Type Marking Code
 YM = Date Code Marking
 Y or Y= Year (ex: E = 2017)
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024
Code	E	F	G	H	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.6 4.9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	40	A

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	162	°C/W
Total Power Dissipation (Note 6)			P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	98	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	T _J = +25°C, V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	0.9	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	20	27	mΩ	V _{GS} = 4.5V, I _D = 6.5A
			26.7	35		V _{GS} = 2.5V, I _D = 5.5A
			49.1	65		V _{GS} = 1.8V, I _D = 3.5A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _D = 5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	485	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	91	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	77	—	pF	
Gate Resistance	R _g	—	3.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	5.9	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	—	12	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.4	—	ns	
Turn-On Rise Time	t _R	—	5.4	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _g = 6Ω, I _D = 1A
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	
Turn-Off Fall Time	t _F	—	9.3	—	ns	
Reverse Recovery Time	t _{RR}	—	7.7	—	ns	I _F = 1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _R	—	1.5	—	nC	I _F = 1.0A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

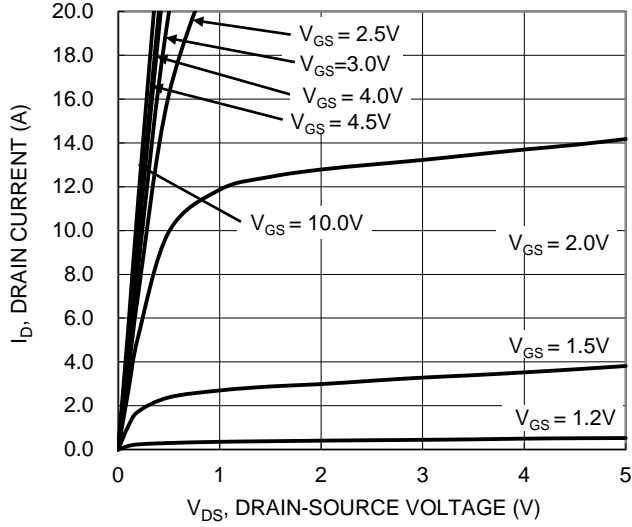


Figure 1. Typical Output Characteristic

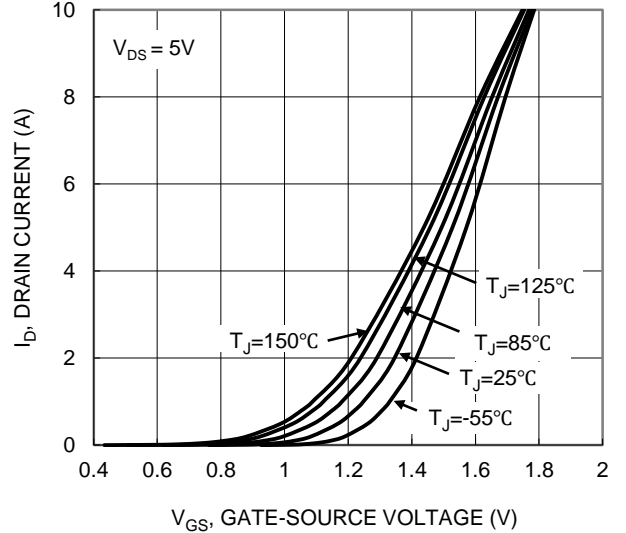


Figure 2. Typical Transfer Characteristic

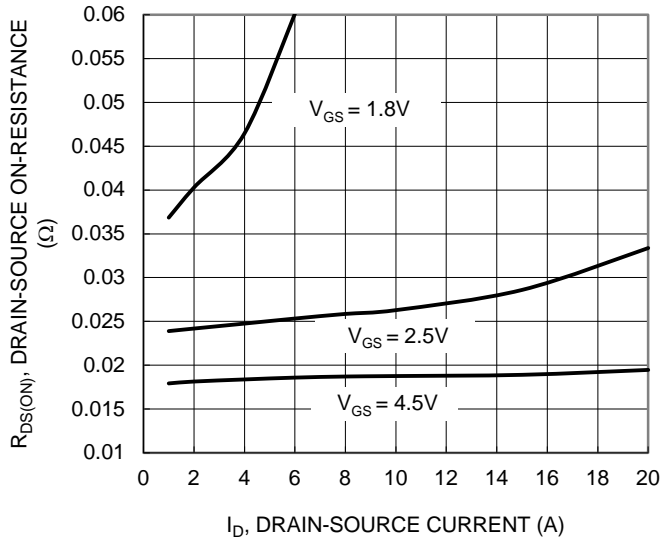


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

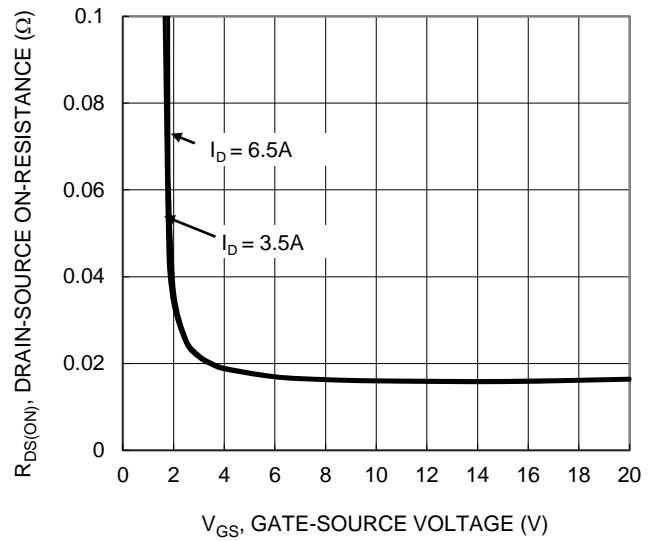


Figure 4. Typical Transfer Characteristic

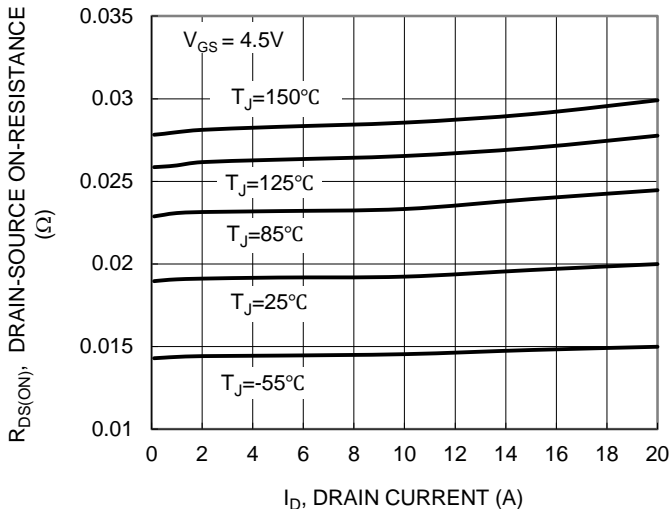


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

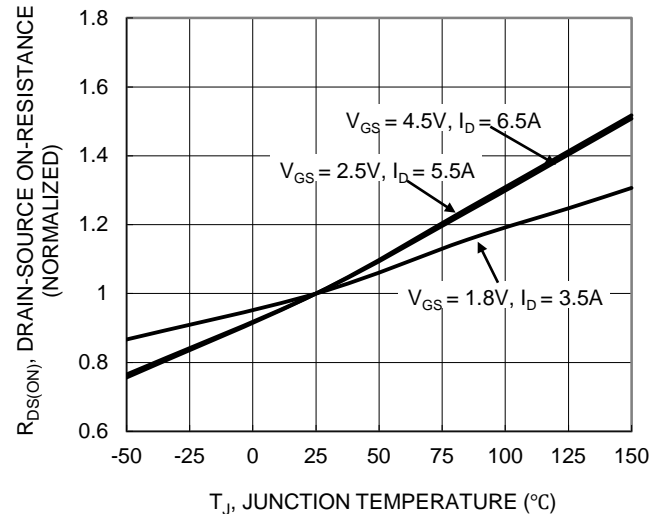


Figure 6. On-Resistance Variation with Junction Temperature

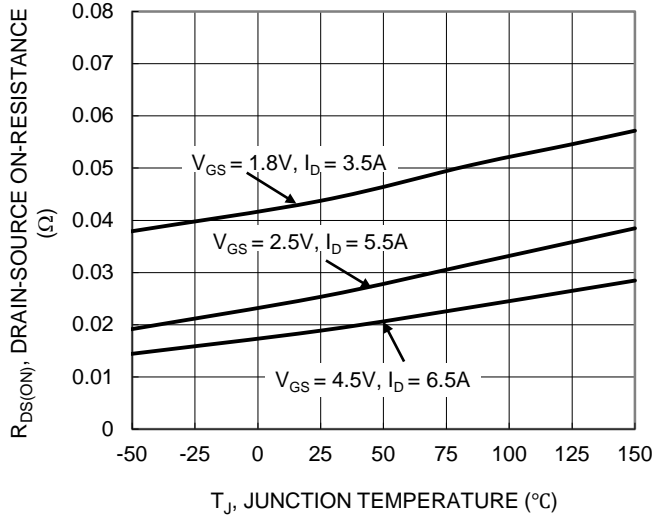


Figure 7. On-Resistance Variation with Junction Temperature

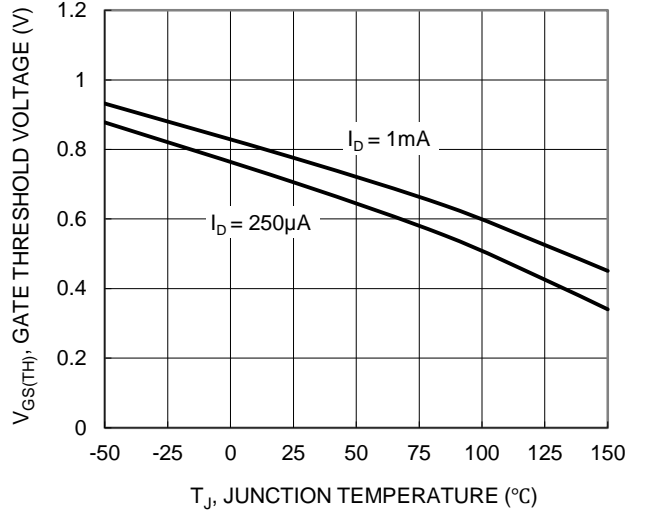


Figure 8. Gate Threshold Variation vs. Junction Temperature

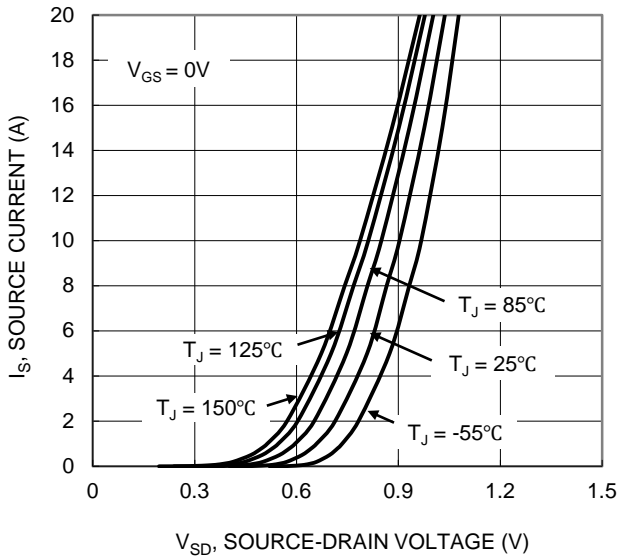


Figure 9. Diode Forward Voltage vs. Current

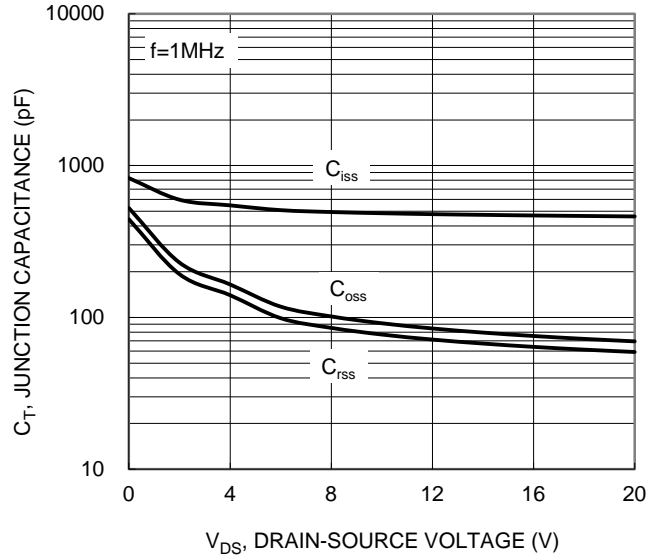


Figure 10. Typical Junction Capacitance

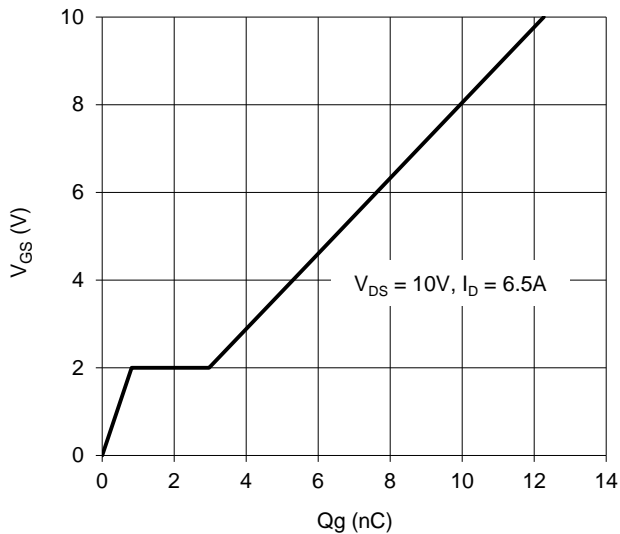


Figure 11. Gate Charge

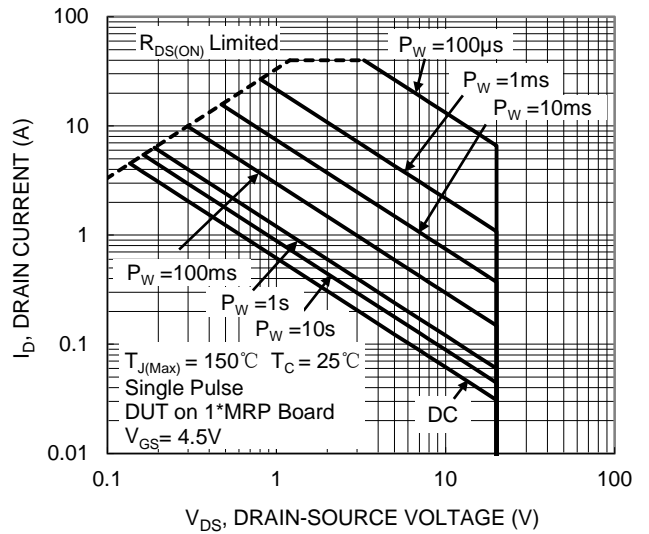


Figure 12. SOA, Safe Operation Area

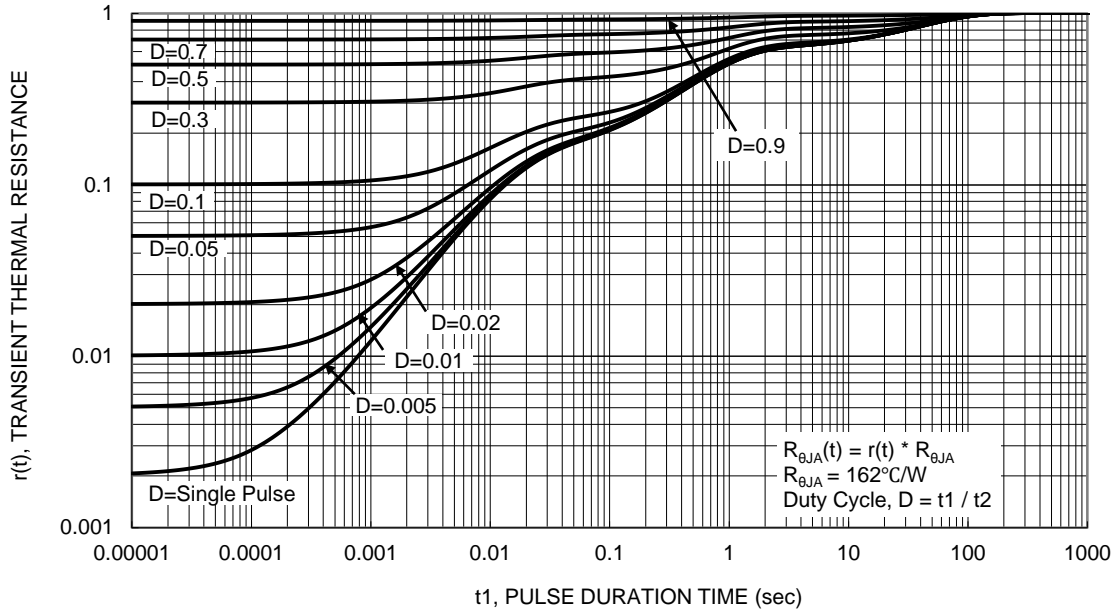
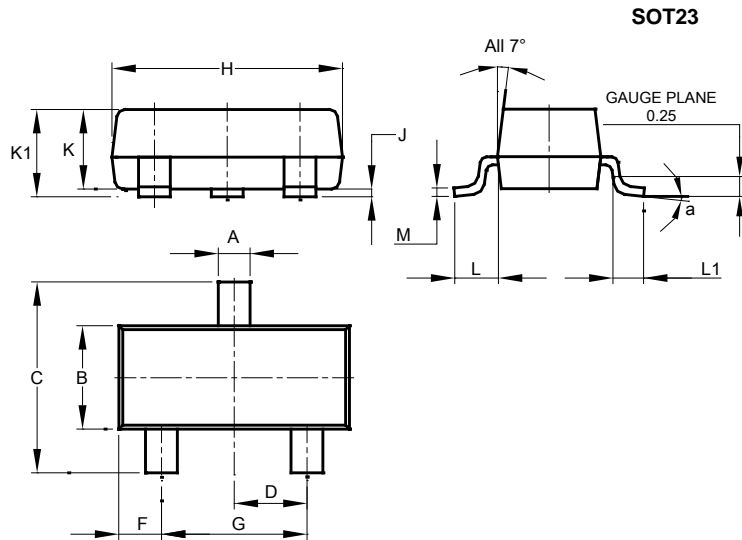


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

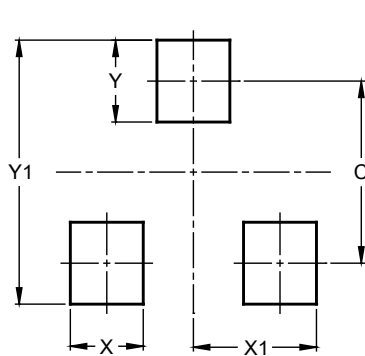
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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